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Table of Content PCIM Asia Shanghai Conference 2025

Keynote

1. **Technology Trends and Future Perspectives of Power Electronics for Electric Vehicles1**
Chang Liu, SuZhou Inovance Automotive Co., Ltd., China

WBG I_SiC

2. **400 V SiC MOSFET Unlocks New Efficiency and Power Density Ranges for Server and AI Power Supply Solutions2**
Owen Song, Infineon Semiconductors (Shenzhen) Company Limited, China
David Meneses, Infineon Technologies Nordic AB, Finland
Ralf Siemieniec, Alex Rossi, Matteo-Alessandro Kutschak, Sriram Jagannath, Infineon Technologies Austria AG, Austria
3. **Impact of P-well Contact on Dynamic Losses in Scaled 1.2 kV SiC MOSFETs for Parallel Switching Applications12**
Paula Reigosa Díaz, Roger Stark, Nick Schneider, Tommaso Stecconi, Lars Knoll, SwissSEM Technologies, Switzerland
Leon Liang, Coris Li, Sun.King Pacific Semiconductor Technology, China



4. **Research on Overcurrent Interruption Capability and Influencing Factors of SiC MOSFETs in DCCBs18**
Xiangyu Wan, Lin Liang, Zhongqi Guo, Imran Zulfiqar, State Key Laboratory of Advanced Electromagnetic Technology, School of Electrical and Electronic Engineering, Engineering Research Center of Power Safety and Efficiency, Ministry of Education of China, Huazhong University of Science and Technology, China



5. **Online Monitoring of SiC MOSFET Junction Temperature with Full-range and Gate oxide Defect Insensitivity.....28**

Dan Zheng, Xuhui Wen, Zhijie Qiu, Hongyang Li, Puqi Ning, Tao Fan,
State Key Laboratory of High Density Electromagnetic Power and
Systems, Institute of Electrical Engineering, Chinese Academy of
Sciences, China
Wenyuan Ouyang, Xiaofeng Jiang, University of Chinese Academy of
Sciences, China

Smart Grid Power Electronics



- 6. A High-Power Step-Up DC Transformer for Renewable Energy
Distribution Systems.....34**
Jiahui He, Ning Wang, Binbin Li, Yingzong Jiao, Dianguo Xu, The School
of Electrical Engineering and Automation, Harbin Institute of Technology,
China



- 7. Design and Testing of 1.44 kVac / 270 Vdc 50 kW Solid-state
Transformer Cell for Data Centers41**
Xin Wu, Haihong Long, Haoxiang Wang, Yi Zhou, Wenxin Wang, Dehong
Xu, College of Electrical Engineering, Zhejiang University, Zhejiang
University, China



- 8. Advanced Energy Management to Effectively Utilize Buildings'
Renewable Energy Generation and Storage Capabilities49**
Christos Mademlis, Evangelos Tsioumas, Nikolaos Jabbour, Despoina
Antoniadou, Vasileios Vlastos, School of Electrical and Computer
Engineering, Aristotle University of Thessaloniki, Greece

- 9. Adaptive Switching Frequency Boundary in Hybrid DCM and BCM
Method for Flyback Micro-Inverter.....59**

Lwena Delgado, Anqi Wang, Chen Xu, Yichen Xu, Shanghai University,
China

Power Si-Devices

10. Superjunction MOSFET with a Trench Contact and Embedded SiO₂ Insulator for Excellent Reverse Recovery69

Rui Li, Keqiang Ma, Fanxin Meng, Xingli Jiang, Min Hu, Chengdu Semi-Future Technology Co., Ltd., China

11. New developed 3.3kV/2.4kA Trench IGBT for Traction application ...74

Xing Chen, Liheng Zhu, Bin Wang, Rongzhen Qin, Qiang Xiao, State key Laboratory of Advanced Power Semiconductor Devices, China

Xing Chen, Liheng Zhu, Bin Wang, Rongzhen Qin, Qiang Xiao, Zhuzhou CRRC Times Semiconductor Co. Ltd., China

12. Plasma Shaping in Silicon Diodes by Cathode-Side Lifetime Recovery79

Nick Schneider, Paula Reigosa Díaz, Tommaso Stecconi, Roger Stark, Lars Knoll, SwissSEM Technologies AG, Switzerland

Coris Li, Leon Liang, Sun.King Pacific Semiconductor Technology, China

13. Benefits of EDT3 750V Technology in Automotive Inverter Applications85

Jiong Wu, Alexandra Bausch, Nebojsa Levkovski, Mathias Geike, Cedric Ouvrard, Infineon Technologies AG, Germany

14. The Impact of Gate Driver Loop Output Capability and Stray Parameters on Switching Performance91

Jie Dong, Infineon Technologies, China

15. Optimized Water Jacket Pin-Fin design for Reducing Pressure Drop in Cooling System97

Juyoung Kim, Monnseok Hong, onsemi, Korea

Roveendra Paul, Leon Zhang, onsemi, USA

16. 1200V and 650V Automotive Power Module Applications in Various EV OBC and DC/DC Converters101

Younhee Lee, BumSeung Jin, Noah Hur, onsemi, USA

Duwon Lee, Kangyoon Lee, Jinwoo Park, Yeriel Bai, Jeongmin Lee, onsemi, Korea

17. New intelligent power module, CIPOS™ Mini DCB IPM with 7th generation IGBTs for motor drive applications.....	108
Bokkeun Song , Jonguk Lee, Kihyun Lee, Taejin Lee, David Jo, Infineon Technologies Korea, South Korea	
WBG Devices	
18. Investigation on Channel Mobility of SiC Trench MOSFET.....	111
Qijun Liu , Yao Yao, Qiming He, Yehui Luo, Guan Song, Yafei Wang, Chengzhan Li, Qiang Xiao, Haihui Luo, Zhuzhou CRRC Times Semiconductor Co., LTD, China	
Qijun Liu , Yao Yao, Qiming He, Yehui Luo, Guan Song, Yafei Wang, Chengzhan Li, Qiang Xiao, Haihui Luo, State Key Laboratory of Power Semiconductor and Integration Technology, China	
19. A Robust and Reproducible Gate Charge Measurement Approach for SiC MOSFET Characterization.....	117
Wenqi Zhou , Tobias Pfletschinger, Lixi Yan, Andreas Hammele, Hadiuzzaman Syed, Karl Oberdieck, Robert Bosch GmbH, Germany	
20. Application of SiC Hybrid Discrete in Photovoltaic and Energy Storage Systems	123
Shuai Cao , Rui Rong, MACMIC SCIENCE&TECHNOLOGY CO., LTD., China	
21. Switching behavior investigation of 1200V CoolSiC™ MOSFET G2 discrete.....	128
Jia Zhao , Infineon Integrated Circuit (Beijing) Co., Ltd., China	
Miaomiao Xiao, Song Shen, Infineon Semiconductors (Shenzhen) Co. Ltd., China	
22. Leveraging Ultra-High Efficiency in High Power Open Frame Flyback Applications	132
Han Cui , Jason Yan, Silvestro Fimiani, United States of America	
23. Low-cost SOI-based level-shift gate driver for high-voltage and >1MHz switching in GaN applications	136
Weidong Chu , Infineon Technologies Americas Corp., USA	
24. Comparative Analysis of Gate Driver Control Topologies: Effects on SiC MOSFET Switching Performance in Half-Bridge Configurations	139

Lan Fang, Venu Gopal Mangal, Robert Bosch GmbH, Germany
Xin Jin, Fangbo Yin, Fangyuan Chen, Bosch, China

- 25. New 1200 V SiC MOSFET-based CIPOS™ Maxi Intelligent Power Module for High-Efficiency Motor Drives 147**
Kihyun Lee, Jinhyeok Kim, Soohyuk Han, Mi-ran Baek, Bokkeun Song,
Infineon Technologies Korea, South Korea

Packaging & Reliability



- 26. Application of Cu Sintering Technology in High-Power-Density Double-Sided Cooling SiC Module..... 153**
Haobin Chen, Haidong Yan, Kuang Sheng, School of Electrical Engineering, Zhejiang University, China

- 27. Investigation of Large Area Solder with TrueHeight™ Preform on Bare Cu Substrates 159**
Liuchang Hu, Damon Hong, Alicia Zhang, Marvin Wang, Macdermid Alpha Electronics Solutions, China
Maurizio Fenech, Macdermid Alpha Electronics Solutions, Germany

- 28. Design and Assessment of Si/SiC Hybrid Power Module With Cu Clip Interconnection for Solar Inverter 164**
Xiankun Zhang, Xiaofei Pan, Xiaodong Zhang, Yuancheng Liu, China Resources Runan Chongqing Co., Ltd., China
Yuxi Liang, Ming Luo, Chongqing University, China

- 29. Influence of the Junction Temperature on the Dynamic Gate Bias Test of SiC MOSFETs 169**
Xiaogang Hu, Qingyuan, Hua, Nanjing NARI Semiconductor Co., Ltd., China
Nan Jiang, Wuxi PowerSemiLab Co., Ltd., China



30. Spatial-Temporal Customizable Topology Graph Networks Combined with LSTM for Power Device RUL Prediction.....174

Xu Gao, Qiang Jia, Fenglei Cao, Yishu Wang, Fu Guo, Beijing University of Technology, China



31. Fault Classification Method for PEMFC Based on Equivalent Circuit and SVM181

Jiahui Zhang, Chenxi Huang, Ruiqin Xia, Hefei University of Technology, China

Power Converter

32. Highly Efficient Auxiliary Power Supply Solution using Infineon ZVS Flyback Controller190

Zhidan Luo, Mingping Mao, Eric Kok, Infineon Technologies Asia Pacific Pte Ltd, Singapore

33. An Optimized Driver Design Strategy for Energy Storage System Applications194

Qibin Wu, Ziqing Zheng, Jie Dong, Infineon Technologies Center of Competence (Shanghai) Co. Ltd., China



34. Realize High Performance 200kVA Auxiliary Power Supply with 1.7kV SiC MOSFET.....201

Jian Sun, Bo Hu, Gaosheng Song, Mitsubishi Electric & Electronics (Shanghai) Co., Ltd., China
Zhengfeng Li, Power Device Works, Mitsubishi Electric Corp., Japan.

35. An active method to solve the touch current issue of totem-pole bridgeless PFC rectifier207

Desheng Guo, Xingqi Chen, Texas Instruments, China
Sean Yu, Texas Instruments, USA

36. High voltage converter input units with improved input current quality212

Yury Skorokhod, Dmitriy Sorokin, Transconverter, Russia Federation
Sergey Volskiy, Moscow Aviation Institute (National Research University),
Russian Federation

37. 48-12 V High Frequency LLC resonant Converter with FPCB Transformer for Data Center218

Si Yao Hu, Naoki Agatsuma, Interdisciplinary Graduate School of
Engineering Sciences, Kyushu University, Japan
Yuta Totoki, Faculty of Engineering, Kyushu University, Japan
Wataru Saito, Shinichi Nishizawa, Research Institute for Applied
Mechanics, Kyushu University, Japan

38. A Dual-phase Interleaved AC Link Converter for HPC Processors .224

Zhaoliang Wen, Dianguo Xu, Harbin Institute of Technology, China

Si Devices

39. A new IGCT Platform for up to 8.5 kV with unprecedented turn-off current capability230

Umamaheswara Vemulapati, Tobias Wikström, Urban Meier, Mark
Frecker, Thomas Stiasny, Christian Winter, Hitachi Energy Ltd.
Semiconductors, Switzerland
Zuzana Ptakova, Hitachi Energy s.r.o., Semiconductors, Czech Republic

40. Enhanced 900 A 1700 V ED Module with Micropattern Trench IGBT for High Performance and Reliability235

Nick Schneider, Rémi Guillemin, Raffael Schnell, Sven Matthias, Chantal
Toker, Lars Knoll, SwissSEM Technologies AG, Switzerland
Ben Gao, Ian Wang, Sunking Pacific Semiconductor Technologies
(Zhejiang) Ltd., China

41. Next Generation 1200V IGBT and Diode Technology for Automotive Drivetrain Applications245

Jiong Wu, Alexander Beckmann, Matteo Dainese, Matthias Fiebig, René
Spence, Infineon Technologies AG, Germany

42. Asymmetric ESD protection in bidirectional trench power MOSFETs for Li-ion battery applications250

Xueqing Liu, Xiaobin Wang, Ji Pan, Sik Lui, Madhur Bobde, Alpha and

Omega Semiconductor, the United States

Packaging & Reliability I

43. Effect of Processing Condition on Reliability Performance of SiC package by Pressure-less Silver Sintering256

Ziying Li, Qingyuan Tang, Bo Luo, Xiangsheng Ma, Guangdong Fenghua Semiconductor Technology Co., Ltd., China

44. Full SiC SLIMDIP for High Efficiency Applications264

Takakura Kazuki, Yuki Terado, Yuya Omagari, Toma Takao, Akiko Goto, Koichiro Nguchi, Mitsubishi Electric Corporation, Japan
Kai Jiang, Xiaoliang Wang, Mitsubishi Electric & Electronics (Shanghai) Co., Ltd., China

45. High Performance Materials Developing for Power Module270

Shihuan Lu, Sumitomo Bakelite (Suzhou) Co., Ltd., China
Yuta Ikari, Go Ichizawa, Sumitomo Bakelite Singapore Pte., Ltd., Singapore

46. All in One Copper Sintering – Die attach and Substrate Attach in Single Step with Soft Tool.....275

Sri Krishna Bhogaraju, CuNex GmbH, Germany
Simon Merkert, Maximilian Rodemers, PINK GmbH Thermosysteme, Germany

Keynote

47. Ultra-Compact and Efficient Power Supply Enabling AI Computing281

Teng Long, University of Cambridge, China

WBG II_GaN

48. System benefit of drone driven by GaN based inverter282

Alan Wai-Keung Lun, Infineon Technologies Hong Kong Limited, HKSAR, China
Marco Cannone, Infineon Technologies Austria AG, Austria
Shawn Wu, Infineon Semiconductors (Shenzhen) Company Limited, China



49. Dynamic On-Resistance Characterization of GaN HEMTs under High Temperature Using Multigroup Double Pulse Test.....289

Xu Jiang, Xinke Wu, Jiahui Sun, College of Electrical Engineering, Zhejiang University, China
Xu Jiang, Xinke Wu, ZJU-Hangzhou Global Scientific and Technological Innovation Center, China
Yuwei Wu, Kevin J. Chen, Department of Electronic and Computer Engineering, The Hong Kong University of Science and Technology, Hong Kong, China

50. 1700V GaN Switch with Adaptive Zero-Voltage Switching for Multi-Output Flyback Converters.....296

Han Cui, Ferhat Tuncer, Yi Li, Power Integrations, United States of America



51. 25kW/L 99.2% Efficiency Wide Output Three-phase PFC based on Modular Inductive Switching Network.....301

Wending Zhao, Xinke Wu, Zhejiang University, China
Wending Zhao, Xinke Wu, ZJU-Hangzhou Global Scientific and Technological Innovation Center, China

Motor Drive & Motion Control

52. Deadbeat predictive Control of Dual Three-Phase Linear Motors Based on Sliding Mode Observer308

Huifei Cheng, Zongbo Hu, Jinsong Kang, College of Transportation, Tongji University, China

53. Dual Position Feedback-Based Oscillation Suppression Method for Full Closed-Loop Position Control315

Xiangrui Xu, Xinyuan Liu, Dianguo Xu, Harbin Institute of Technology, China



54. A Flexible Operated Li-ion Battery Management System for Motor Drives in Electric Vehicle Applications322

Christos Mademlis, Nikolaos Jabbour, Evangelos Tsioumas, School of Electrical and Computer Engineering, Aristotle University of Thessaloniki, Greece

55. Artificial Intelligence Augmented P(AI)D Cycle-by-Cycle Controller for Automotive DC-DC Converter Applications Based on AURIX TC4x.....332

Mihail Jefremow, Aziz Banna, Juergen Schaefer, Arndt Voigtlaender, Infineon Technologies, Germany
Alberto Trentin, Infineon Technologies, Italy

Motor Control

56. Double-Ratio Based PI Parameters Design Method of Two-Mass Speed loop System337

Pengcheng Lan, Ming Yang, School of Electrical Engineering and Automation, Harbin Institute of Technology, China
Xinmei Zhang, Ningbo Anson CNC Technology Co., Ltd, China
Zhenhua Lv, Beijing Institute of Control Engineering, China

57. Ellipse Condition Based Controller Parameter Tuning for Refined Stability Performance.....342

Pengcheng Lan, Ming Yang, School of Electrical Engineering and Automation, Harbin Institute of Technology, China
Xinmei Zhang, Ningbo Anson CNC Technology Co., Ltd, China
Zhenhua Lv, Beijing Institute of Control Engineering, China

58. Research on narrow pulse suppression strategy of three-level inverter based on dual modulation wave CBPWM348

Xudong Bai, Guodong Yu, Harbin Institute of Technology, China

59. A Comprehensive Review of the Longitudinal End Effects in Linear Motors353

Bining Liu, Jingsong Kang, College of Transportation, Tongji University, China

60. Parameter Identification of Robotic Joint with Harmonic Drive361

Xinyuan Liu, Xiangrui Xu, Dianguo Xu, Harbin Institute of Technology, China



61. PDC-Based Hybrid Flux Observer with Flux Error Estimation for Sensorless SPMSM Drives366

Xubo Gong, Wei Wang, Harbin Institute of Technology, China

62. Resonance Ratio Control for Vibration and Disturbance Suppression in Force Servoing374

Zhiyu Zhang, Ming Yang, Pengcheng Lan, Harbin Institute of Technology, China

Xinmei Zhang, Ningbo Anson CNC Technology Co., Ltd, China

Zhenhua Lv, Beijing Institute of Control Engineering, China

63. Optimization method of stator winding temperature model of permanent magnet synchronous motor381

Songze Zhao, Puqi Ning, Tao Fan, Xiaoshuang Hui, University of Chinese, Institute of Electrical Engineering, Chinese Academy of Sciences, Key Laboratory of Power Electronics and Electric Drive, Institute of Electrical Engineering, Chinese Academy of Sciences, Collaborative Innovation Center of Electric Vehicles in Beijing, China

High Frequency Power Converter



64. Reducing the Size and Weight of Filter Inductor for NPC 3-Level Inverter with 240CPWM387

Jiaxuan Yu, Jiaao Xu, Deliang Wu, Shanghai University, China

65. Comparative Analysis on Series Resonant Converter and CLLC Resonant Converter for Micro-Inverter Application396

Chaojie Zhu, Deliang Wu, Shanghai University, China

66. Small Signal Models of Wireless Power Transfer Converters for Unmanned Vehicles Charging Stations405

Nikolay Kalugin, Aleksei Chernyshov, Egor Zhuchenko, Energet LLC, Russia
Aleksei Chernyshov, Skolkovo Institute of Science and Technology, Russia

67. Isolated Bi-directional Grid-connected Micro-inverter Based on Series Resonant Converter411

Deliang Wu, Motuma Adula Dabis, Chaojie Zhu, Shanghai University, China

68. Multi-functional chip contributes to the compact design of automotive SiC power module419

Lizhong Zhao, Hongguang Huang, Mitsubishi Electric & Electronics (Shanghai) Co., Ltd., China
Kentaro Yoshida, Power Device Works, Mitsubishi Electric Co., Ltd., Japan

69. Optimized Extended Phase Shift Modulation for Dual Active Bridge Converters in Automotive Battery Systems424

Jiaming Wang, Yanmin Wang, Weiqi Zhang, Harbin Institute of Technology, China



70. Multi-Objective Optimization Design of Dual-Bridge Series Resonant Converter Based on Deep Reinforcement Learning431

Xiang Pan, Zhicheng Gao, Jianing Wang, Hefei University of Technology, China
Tianyi Ren, Zhiyuan Wang, Sungrow Power Supply Company, China

71. Fast Charging Station for Simultaneous Recharging of Three Electric Vehicles437

Nikolay Volskiy, Michail Krapivnoi, Charge Evolution Ltd, Russian Federation

Smart Grid & Energy Transmission

72. New Generation Ultra High Power Semiconductors for VSC-HVDC Applications443

Evgeny Tsyplakov, David Guillon, L. Santolaria, H. Beyer, A. Roesch, Christian Winter, Makan Chen, Hitachi Energy Ltd. Semiconductors, Switzerland
Jan Vobecky, Hitachi Energy s.r.o. Semiconductors, Czech Republic

73. Performance Analysis of Basic and Active Neutral Point Clamped Inverter for Energy Storage System449

Andrew Yang, onsemi, Republic of Korea
Lei Yang, Yi Liu, onsemi, China

74. High Efficiency SiC MOSFET Solutions for Solar System454

Wenmin Hua, Lifeng Chen, Infineon Technologies Center of Competence (Shanghai) Co. Ltd., China



75. Probability Predication of Electric Vehicle Schedulable Capacity Based on Improved Informer with Copula.....459

Zhibo Liu, Meiqin Mao, Yan Du, Research Center for Photovoltaic System Engineering, Ministry of Education, Hefei University of Technology, China
Cheng Yang, State Grid Anhui Electric Power Co., Ltd, China
Yuanyue Wang, Minglei Zhu, State Grid Anhui Electric Vehicle Service Co., Ltd, China
Nikos Hatziaargyriou, National Technical University of Athens, Greece

76. A Comparative Evaluation of Efficiency and Volume for Monolithic Rectifier and Solid-State Transformer465

Ruiye Li, Ning Wang, BinBin Li, Dianguo Xu, School of Electrical Engineering, Harbin Institute of Technology, China

77. The Economical Solution of Offshore HVDC for Wind Power Integration and Performance Comparison471

Zuoyu Wei, Infineon Technologies (Xi'an) Co., Ltd., China
Heng Wang, Infineon Integrated Circuit (Beijing) Co., Ltd., China
Yuwei Lu, Infineon Technologies Center of Competence (Shanghai) Co.

Ltd., China

SiC related hybrid switch

78. Introducing a new 650 V SOI Gate Driver with Improved DESAT Protection.....478

Zhou Chen, Mercedes Labella, Gianluca Mele, Infineon Technologies Americas Corp., the United States

79. FusionPlus – Novel Hybridswitch to improve efficiency and reduce system cost in 800V battery vehicles inverter483

Norbert Pluschke, CN-iCuTech Semiconductor Hongkong, HKSAR, China
Carl Yang, YiTong Semiconductor, China

80. Practically achievable WLTC loss improvements for the Si/SiC hybrid switch approach in a 400 V automotive traction inverter application – a retrofitting case study487

Hariprasad Baburajan, Alexander Bucher, Christian Hasenohr, Alexander Rambatius, Mohadeseh Jahani, Sabarinadh Pamarathi, Valeo eAutomotive Germany GmbH, Germany

81. Active DC-Link capacitor discharge methods with Si/SiC Fusion power module for addressing vehicle cost down.....497

Tomas Reiter, Julius Schapdick, Michael Krug, Matthias Weinmann, Infineon Technologies AG, Neubiberg, Germany
Michael Niendor, Infineon Technologies AG, Warstein, Germany

Packaging & Reliability II

82. Analysis and Study on the Advantages of one Innovative SiC Chip Embedding PCB Solution for xEV Main Inverter Application506

Hao Zhang, Wen Xu, Xiaobo Jing, Infineon Technologies China Co., Ltd. Shanghai, China
Ippisch Matthias, Fontana Nico, Infineon Technologies AG, Germany



83. 3D Wiring Technology Development for Power Modules to Achieve High-Power Density.....512

Akito Nakagome, T. Watakabe, Souta Yamaguchi, Yuichiro Hinata,
Hiromichi Gohara, Shinichiro Adachi, Yoshinari Ikeda, Hirohisa Ooyama,
Fuji Electric Co., Ltd., Japan

**84. Advanced cooling of power electronics with copper cold sprayed
aluminum heatsinks & busbars.....517**

Michael Dasch, Reeti Singh, Ján Kondás, Max Meinicke, Leonhard
Holzgaßner, Markus Brotsack, Impact Innovations, Germany

**85. Increased power density and lifetime of thin automotive inverter
chips through Cu bonding.....522**

Maria Spies, Matthias Fiebig, Tomas Reiter, Mark Muenzer, Infineon
Technologies AG, Neubiberg, Germany
Michael Niendorf, Matthias Fiebig, Matthias Lassmann, Dennis Bräker,
Marc Tuellmann, Nikolaj Gorte, Infineon Technologies AG, Warstein,
Germany
Mohamed Salleh, Mohamed Saheed, Infineon Technologies Sdn. Bhd.,
Kulim, Malaysia

Keynote

86. Evolutionary Trends in Power Supply for AI Data Centers529

Speaker: Zhaozheng Hou, Huawei Digital Power, China

Special Session

**“Power Chiplet” technology, ultra-high-power density platform for future
power electronics**

**87. Power Chiplet Technology for Next Generation Power Electronics
Systems.....530**

Ichiro Omura, Kyushu Institute of Technology, Japan

88. Advanced Packages with Power-On-Substrate Solutions531

Frye Fung, ACCESS Semiconductor Co., Ltd., China

89. Chip Embedded Panel Level Power Package for AI and Vehicles...532

Yoshiaki Aizawa, AOI ELECTRONICS CO., LTD., Japan

**90. Novel Integration Concepts for Power Electronics – Embedding of
SiC MOSFET for High-performance Power Modules533**

Lars Boettcher, Fraunhofer IZM Berlin, Germany

Advanced low power Module Design

- 91. Inductor-Induced Oscillations in SiC Device Characterization: A Comparative Study534**
Nguyen-Nghia Do, Jung-Pei Cheng, Yu-Ming Chen, Chen-Min Chen, Sheng-Tsai Wu, Tai-Jyun Yu, Cheng-Han Tsai, Jing-Yao Chang, Jung-Hsuan Chen, Wei-Zhong Huang, PowerX Semiconductor, Taiwan, China
- 92. New Transfer-Molded Compact DIIPM™542**
Takamasa Miyazaki, Naoki Ikeda, Shuhei Yokoyama, Hiroyuki Nakamura, Masataka Shiramizu, Mitsubishi Electric Corporation, Japan
Hongguang Huang, Mitsubishi Electric & Electronics (Shanghai) Co., Ltd., China
- 93. Thermal Performance Analysis and Study on one Top Side Cooling discrete package for xEV OBC Application.....548**
Jiming Li, Shaoyang Li, Hao Zhang, Xiaobo Jing, Infineon Technologies China Co., Ltd., China
- 94. SiC MOSFET based CCM Totem-pole PFC with Ultra-slim Design .553**
Guoxing Zhang, Zan Wang, Infineon Technologies, China
Pengcheng Bai, Infineon Technologies, Singapore
- 95. Voltage Derating Behavior of High Temperature Capacitors for DC-Link Applications558**
Adel Bastawros, SABIC, USA
Yuan Zhou, SABIC, China
Fumio Yu, SABIC, Japan
Takeshi Horiguchi, Takashi Mori, Kenichi Oshita, Nichicon, Japan